UNR32AV

Silicon NPN epitaxial planar type

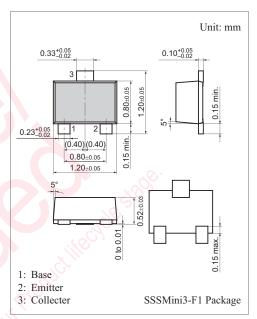
For digital circuits

■ Features

- Suitable for high-density mounting and downsizing of the equipment
- Contribute to low power consumption

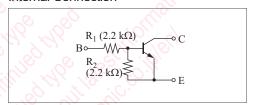
■ Absolute Maximum Ratings $T_a = 25$ °C

| Parameter | Symbol | Rating | Unit | |
|---------------------------------------|------------------|-------------|------|--|
| Collector-base voltage (Emitter open) | V_{CBO} | 50 | V | |
| Collector-emitter voltage (Base open) | V _{CEO} | 50 | V | |
| Collector current | I_{C} | 80 | mA | |
| Total power dissipation | P_{T} | 100 | mW | |
| Junction temperature | T _j | 125 | °C | |
| Storage temperature | T _{stg} | -55 to +125 | °C | |



Marking Symbol: KP

Internal Connection

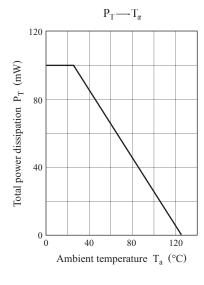


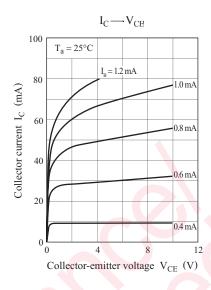
■ Electrical Characteristics T_{a'} = 25°C±3°C

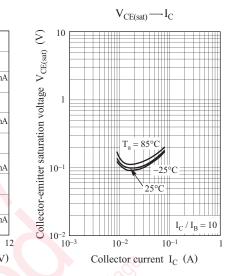
| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|--|----------------------|--|------|-----|------|------|
| Collector-base voltage (Emitter open) | V_{CBO} | $I_{\rm C} = 10 \mu \text{A}, I_{\rm E} = 0$ | 50 | | | V |
| Collector-emitter voltage (Base open) | V _{CEO} | $I_{\rm Cl} = 2 \text{ mA}, I_{\rm B} = 0$ | 50 | | | V |
| Collector-base cutoff current (Emitter open) | I_{CBO} | $V_{CB} = 50 \text{ V}, I_{E} = 0$ | | | 0.1 | μΑ |
| Collector-emitter cutoff current (Base open) | I _{CEO} | $V_{CH} = 50 \text{ V}, I_{B} = 0$ | | | 0.5 | μΑ |
| Emitter-base cutoff current (Collector open) | I_{EBO} | $V_{EB} = 6 \text{ V, } I_{C} = 0$ | | | 2.0 | mA |
| Forward current transfer ratio | h _{FE} | $V_{CH} = 10 \text{ V}, I_{C} = 5 \text{ mA}$ | 6 | | 20 | |
| Collector-emitter saturation voltage | V _{CE(sat)} | $I_{\rm CI} = 10 \text{ mA}, I_{\rm B} = 1.5 \text{ mA}$ | | | 0.25 | V |
| Output voltage high-level | V_{OH} | $V_{CCI} = 5 \text{ V}, V_B = 0.5 \text{ V}, R_{LI} = 1 \text{ k}\Omega$ | 4.9 | | | V |
| Output voltage low-level | V _{OL} | $V_{CCI} = 5 \text{ V}, V_B = 2.5 \text{ V}, R_{LI} = 1 \text{ k}\Omega$ | | | 0.2 | V |
| Input resistance | R_1 | | -30% | 2.2 | +30% | kΩ |
| Resistance ratio | R_1/R_2 | | 0.7 | 1.0 | 1.3 | _ |
| Transition frequency | f_T | $V_{CB} = 10 \text{ V}, I_{E} = -2 \text{ mA}, f = 200 \text{ MHz}$ | | 150 | | MHz |

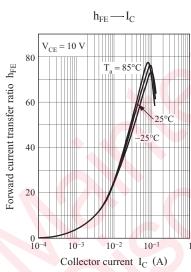
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

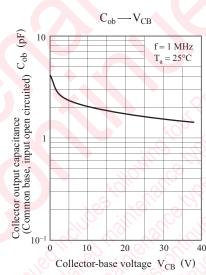
UNR32AV Panasonic

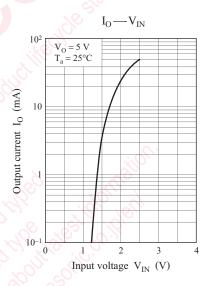


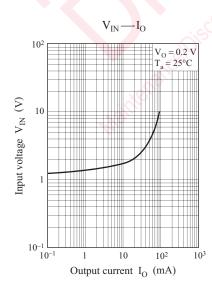












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